

# **isc Silicon NPN Power Transistor**

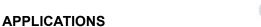
# **MJ16110**

#### **DESCRIPTION**

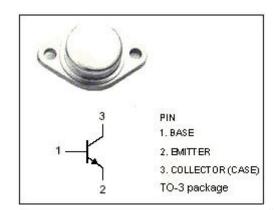
Collector-Emitter Sustaining Voltage-

V<sub>CEO(SUS)</sub>= 400V(Min)

- · High Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



 Designed for use in half bridge and full bridge off line converters.

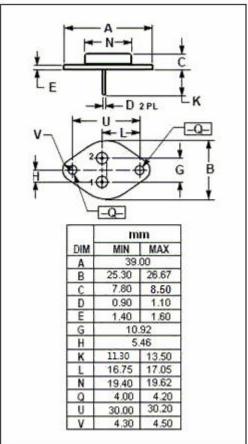


# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER		VALUE	UNIT	
V <sub>CES</sub>	Collector-Emitter Voltage	650	V		
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V		
V <sub>EBO</sub>	Emitter-Base Voltage	6	V		
Ic	Collector Current-Continu	15	Α		
I <sub>CM</sub>	Collector Current-Pulsed	20	Α		
I <sub>B</sub>	Base Current-Continuous	10	Α		
I <sub>BM</sub>	Base Current-Pulsed	15	Α		
P <sub>D</sub>	Total Power Dissipation	T <sub>C</sub> =25℃ T <sub>C</sub> =100℃	175 100	W	
Tj	Junction Temperature		200	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature		-65~200	$^{\circ}$	

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT	
R <sub>th j-C</sub>	ThermalResistance Junction To Case	0.92	°C/W	



isc Website: www.iscsemi.com



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#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 20mA; I <sub>B</sub> =0	400			V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> =5A ;I <sub>B</sub> =0.5A			0.9	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A ;I <sub>B</sub> = 1.2A			2.0	V
V <sub>CE(sat)-3</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A ;I <sub>B</sub> = 2A I <sub>C</sub> = 10A ;I <sub>B</sub> = 2A;T <sub>C</sub> =100°C			1.0 1.5	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A ;I <sub>B</sub> = 2A I <sub>C</sub> = 10A ;I <sub>B</sub> = 2A;T <sub>C</sub> =100°C			1.5 1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CBO</sub> =650V,I <sub>E</sub> =0; V <sub>CBO</sub> =650V,I <sub>E</sub> =0;T <sub>C</sub> =100°C			0.1 1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> =0			10	μА
h <sub>FE</sub>	DC Current Gain	Ic= 15A; Vc==5V	6		20	

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